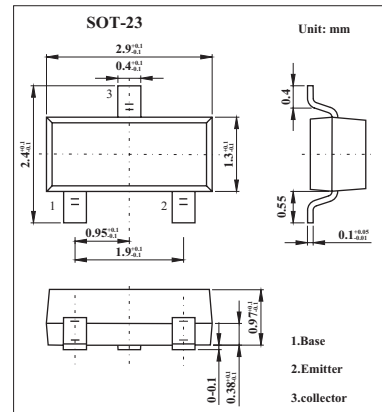


PNP Epitaxial Planar Silicon Transistors

2SB1295

■ Features

- Large current capacity.
- Low collector to emitter saturation voltage.
- Very small-sized package permitting sets to be made smaller and slimer.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-15	V
Collector-emitter voltage	V_{CEO}	-15	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-0.8	A
Collector current (pulse)	I_{CP}	-3	A
Collector dissipation	P_C	200	mW
Jumction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -12V, I_E = 0$			-100	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-100	nA
DC current Gain	h_{FE}	$V_{CE} = -2V, I_C = -50mA$	135		600	
Gain bandwidth product	f_T	$V_{CE} = -2V, I_C = -50mA$		300		MHz
Output capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz$		15		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5mA, I_B = -0.5mA$		-10	-25	mV
	$V_{CE(sat)}$	$I_C = -400mA, I_B = -20mA$		-100	-200	mV
Base-to-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -400mA, I_B = -20mA$		-0.9	-1.2	V
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-15			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = \infty$	-15			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V

■ hFE Classification

Marking	UL		
Rank	5	6	7
hFE	135~270	200~400	300~600